

**APPARATUS AND PROCESS FOR THE PREPARATION
OF LOW-IRON SINGLE CRYSTAL SILICON SUBSTANTIALLY
FREE OF AGGLOMERATED INTRINSIC POINT DEFECTS**

ABSTRACT OF THE DISCLOSURE

5 A method and apparatus for producing silicon single
crystals with reduced iron contamination is disclosed.
The apparatus contains at least one structural component
constructed of a graphite substrate and a silicon carbide
protective layer covering the surface of the substrate
10 that is exposed to the atmosphere of the growth chamber.
The graphite substrate has a concentration of iron no
greater than about 1.5×10^{12} atoms/cm³ and the silicon
carbide protective layer has a concentration of iron no
greater than about 1.0×10^{12} atoms/cm³.